October 1996



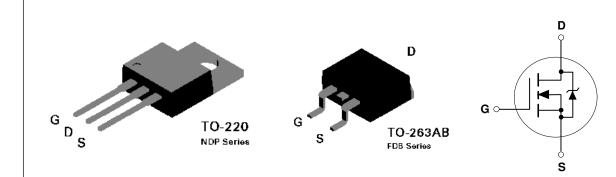
# NDP5060 / NDB5060 N-Channel Enhancement Mode Field Effect Transistor

#### **General Description**

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

#### Features

- 26 A, 60 V.  $R_{DS(ON)} = 0.05 \Omega @ V_{GS} = 10 V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- TO-220 and TO-263 (D<sup>2</sup>PAK) package for both through hole and surface mount applications.



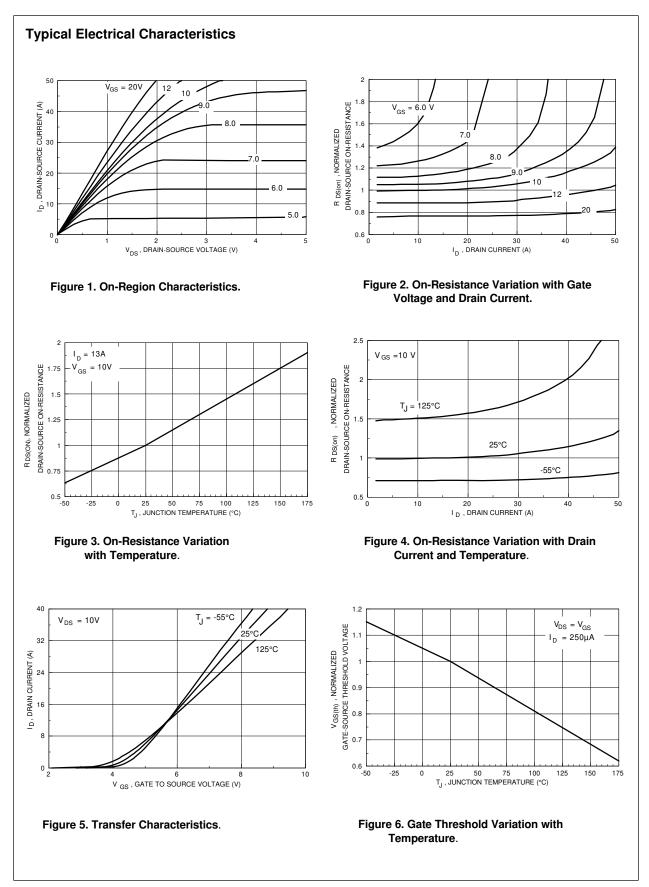
# **Absolute Maximum Ratings** T<sub>c</sub> = 25°C unless otherwise note

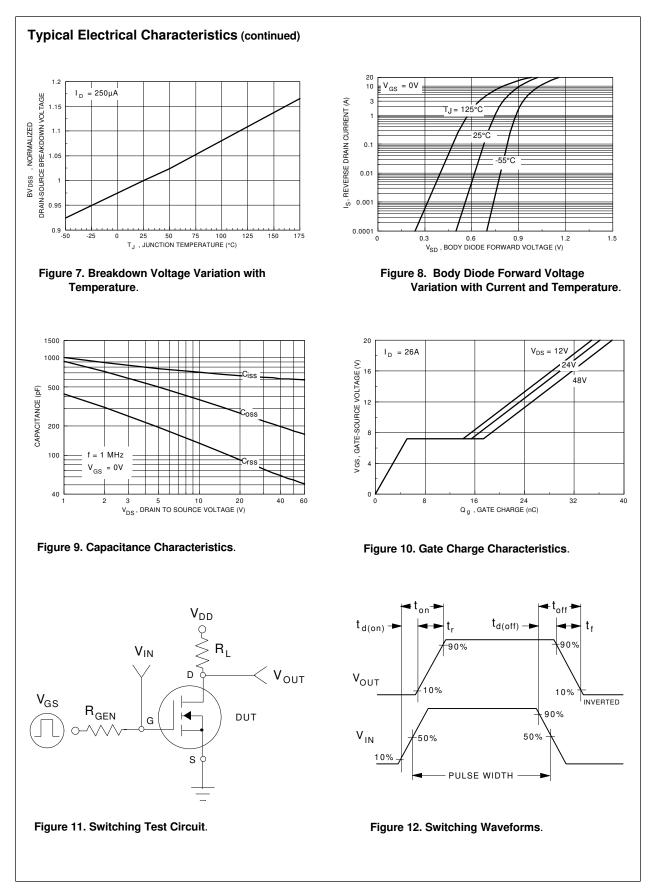
Symbol	Parameter	NDP5060	NDB5060	Units	
V <sub>DSS</sub>	Drain-Source Voltage	60		V	
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \le 1 M\Omega$ )	60		V	
V <sub>GSS</sub>	Gate-Source Voltage - Continuous	±20		V	
	- Nonrepetitive ( $t_P < 50 \ \mu s$ )	±40			
I <sub>D</sub>	Drain Current - Continuous	26		Α	
	- Pulsed	78			
P <sub>D</sub>	Total Power Dissipation @ $T_c = 25^{\circ}C$	68	68		
	Derate above 25°C	0.45	W/°C		
T_,T <sub>STG</sub>	Operating and Storage Temperature Range	-65 to	175	°C	

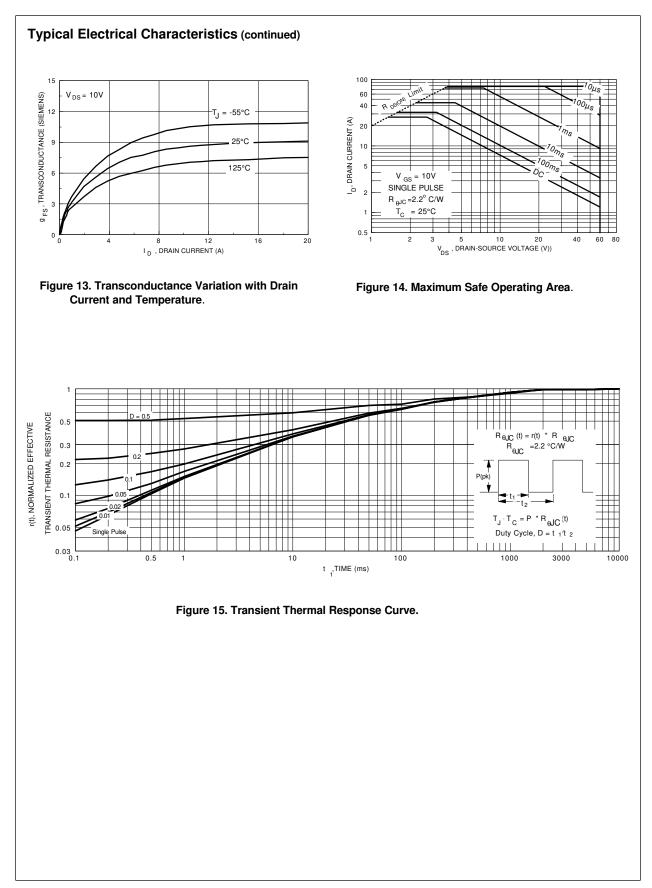
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)	·				•	
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 30$ V, $I_{D} = 26$ A				100	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Curre	ent				26	А
OFF CH/	ARACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$				250	μA
		٦ ٦	Г <sub>J</sub> = 125°С			1	mA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				100	nA
	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAI	RACTERISTICS (Note 1)						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\rm DS} = V_{\rm GS}, I_{\rm D} = 250 \mu {\rm A}$		2	2.9	4	V
			T <sub>J</sub> = 125°C	1.4	2.2	2.8	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 13 \text{ A}$ $T_{J} = 125^{\circ}\text{C}$			0.04	0.05	Ω
				0.07	0.08		
l <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V		26			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 13 \text{ A}$			9		S
DYNAMI	C CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			630		pF
C <sub>oss</sub>	Output Capacitance				225		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				70		pF
	NG CHARACTERISTICS (Note 1)				1		
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 26 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 15 \Omega$			9	20	nS
t,	Turn - On Rise Time				95	200	nS
t <sub>D(off)</sub>	Turn - Off Delay Time				19	40	nS
t <sub>f</sub>	Turn - Off Fall Time				48	100	nS
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 24 V,$ $I_{D} = 26 A, V_{GS} = 10 V$			20	40	nC
Q <sub>gs</sub>	Gate-Source Charge				5		nC
Q <sub>gd</sub>	Gate-Drain Charge				11		nC

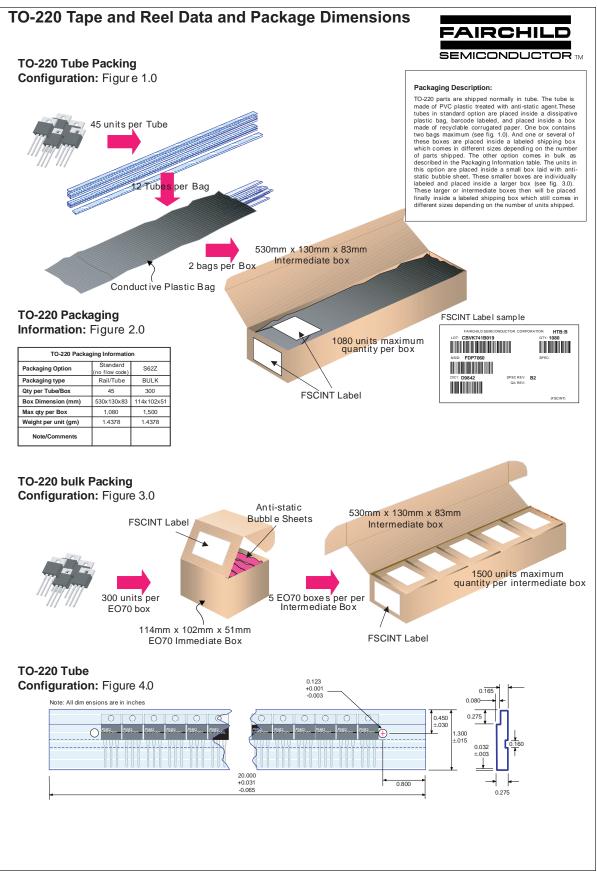
Electrical Characteristics (T <sub>c</sub> = 25°C unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE DIODE CHARACTERISTICS					
I <sub>s</sub>	Maximum Continuos Drain-Source Diode Forward Current				26	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				78	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{\rm GS} = 0 \ V, \ I_{\rm S} = 13 \ A \ ({\rm Note \ 1})$		0.9	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 26 A,$ $dI_F/dt = 100 A/\mu s$		54	120	ns
l <sub>rr</sub>	Reverse Recovery Current			2.1	8	Α
THERMA	L CHARACTERISTICS	•	·	•		
R <sub>ØJC</sub>	Thermal Resistance, Junction-to-Case				2.2	°C/W
R <sub>øja</sub>	Thermal Resistance, Junction-to-Ambient				62.5	°C/W

Note: 1. Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%.

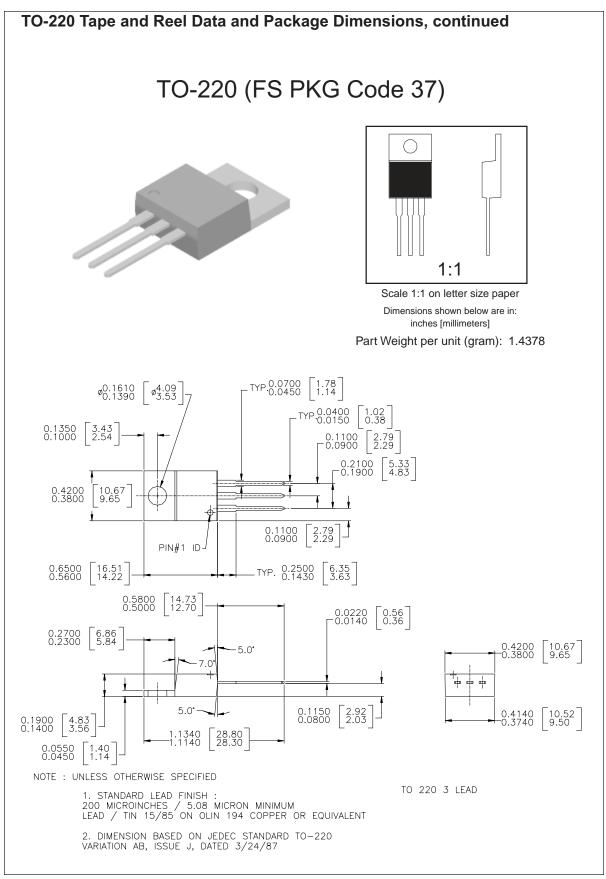




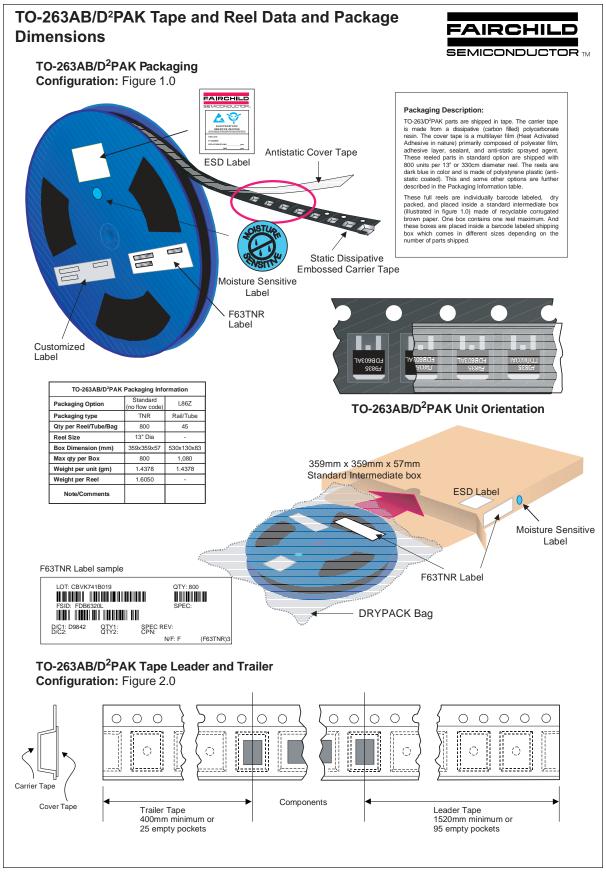




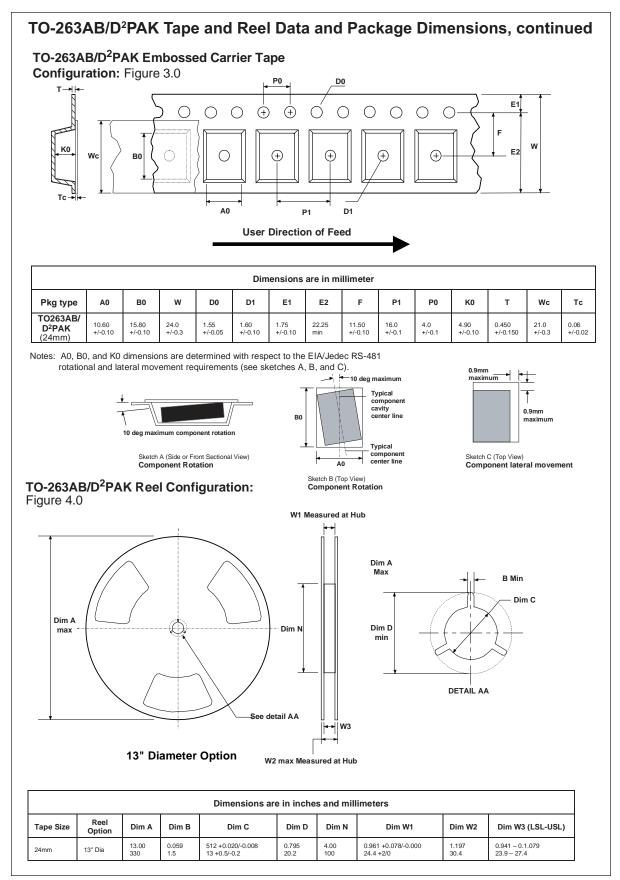
August 1999, Rev. B

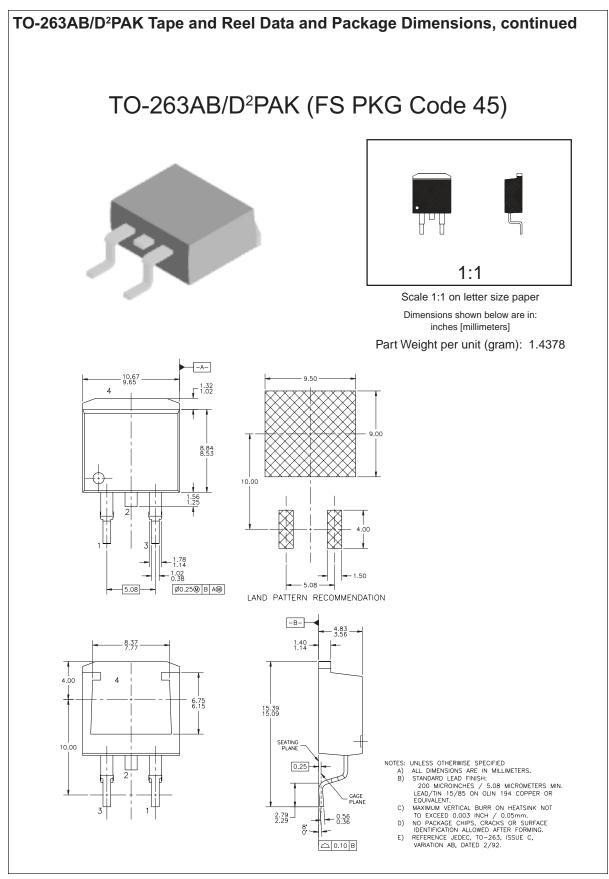


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

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